



### **STP11NM50N Information**



For Reference Only

Part Number STP11NM50N

Manufacturer STMicroelectronics

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 500V 9A TO-220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## **STP11NM50N Specifications**

Manufacturer Part Number         STP11NM50N           Manufacturer         STMicroelectronics           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         MDmesh? II           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         8.5A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         19nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         \$47pF @ 50V           Vgs (Max)         \$±25V           FET Feature         -           Power Dissipation (Max)         70W (Tc)           Rds On (Max) @ Id, Vgs         470 mOhm @ 4.5A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB           Package / Case         TO-220-3		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         MDmesh? II           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         8.5A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         19nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         547pF @ 50V           Vgs (Max)         ±25V           FET Feature         -           Power Dissipation (Max)         70W (Tc)           Rds On (Max) @ Id, Vgs         470 mOhm @ 4.5A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB           Package / Case         TO-220-3	Manufacturer Part Number	STP11NM50N
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C8.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs19nC @ 10VInput Capacitance (Ciss) (Max) @ Vds547pF @ 50VVgs (Max)±25VFET Feature-Power Dissipation (Max)70W (Tc)Rds On (Max) @ Id, Vgs470 mOhm @ 4.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C8.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs19nC @ 10VInput Capacitance (Ciss) (Max) @ Vds547pF @ 50VVgs (Max)±25VFET Feature-Power Dissipation (Max)70W (Tc)Rds On (Max) @ Id, Vgs470 mOhm @ 4.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Series	MDmesh? II
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Current - Continuous Drain (Id) @ 25°C  Bish (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  470 mOhm @ 4.5A, 10V  Operating Temperature  Supplier Device Package  Package / Case  8.5A (Tc)  9.04  9.05  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07  9.07	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  A70 mOhm @ 4.5A, 10V  Operating Temperature  Supplier Device Package  Package / Case  TO-220AB  TO-220-3	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id	Current - Continuous Drain (Id) @ 25°C	8.5A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  547pF @ 50V  Vgs (Max)  ±25V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  470 mOhm @ 4.5A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  Package / Case  TO-220AB  TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  EET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Through Hole  Supplier Device Package  Package / Case  TO-220-3	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±25VFET Feature-Power Dissipation (Max)70W (Tc)Rds On (Max) @ Id, Vgs470 mOhm @ 4.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	19nC @ 10V
FET Feature - Tower Dissipation (Max) 70W (Tc) Rds On (Max) @ Id, Vgs 470 mOhm @ 4.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	547pF @ 50V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  470 mOhm @ 4.5A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220AB  Package / Case  TO-220-3	Vgs (Max)	±25V
Rds On (Max) @ Id, Vgs470 mOhm @ 4.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220AB  Package / Case  TO-220-3	Power Dissipation (Max)	70W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	470 mOhm @ 4.5A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

#### **STP11NM50N Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

# STP11NM50N Payment Methods



















### **STP11NM50N Shipping Methods**













If you have any question about STP11NM50N, please do not hesitate to contact us!

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